



LD808-2000-3

LD808-3000-3

●Specifications:

Wavelength: 808nm

Power: 2W, 3W CW

Package: C-Mount, TO3

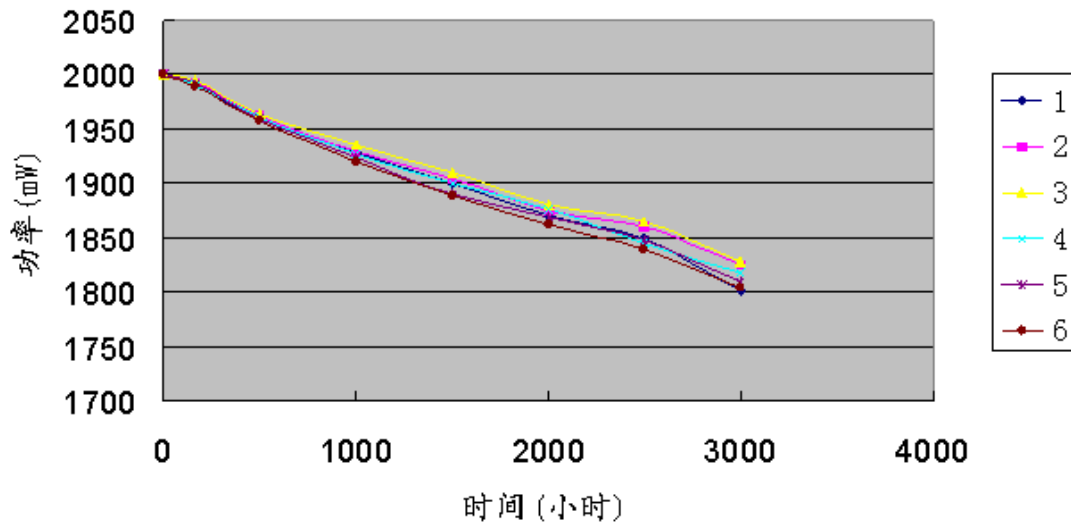
●Electrical and Optical Characteristics($T_c=25^\circ\text{C}$):

Parameter		Symbol	LD808-2000	LD808-3000	Unit
Lasing Wavelength		λ_p	808 \pm 5		nm
Power		P_o	2	3	W
Threshold Current		I_{th}	≤ 0.8	≤ 1	A
Operating Current		I_{op}	≤ 2.6	≤ 3.5	A
Operating voltage		V_{op}	≤ 2.2		V
Emission Area		-	150x1		μm^2
Beam ¹⁾ Divergence	Parallel	$\theta_{//}$	12		deg.
	Perpendicular	θ_{\perp}	12		deg.
Slope Efficiency		η	≤ 1.1		mW/mA
Series Resistance		R_d	≤ 0.25		Ω
Polarization Direction			TE		

1) Full angle at half Maximum



●Lifetime



●Lifetime Reliability data

Tested sample description	random sample from bulk production
Test condition:	
Amount of tested laserdiodes	20
Mean time of operation	5000
Total time of operation	96000
Amount of failed units and description of failure (random or degradation)	1.67*10 ⁴ Fit Random
Operation conditions during test: Power Temperature of chip base	CW 2.4A (constant current) (25±3) °C
Lifetest analysis data:	
Mean time to failure (MTTF) for random failure	18045hrs(α=90%)
B10 for random failure	4000hrs
Mean time to failure (MTTF) for degradation (extrapolate time to 20% power drop)	14285hrs
B10 for degradation (extrapolate time to 20% power drop)	6000hrs